INFORMATION DRAW Serial No. 10/765,894 Afty. Docket No. 042069 **DISCLOSURE** Applicant(s): Yasuyuki TAMURA et al. CITATION PTO-1449 Group Art Unit: Unassigned Filing Date: January 29, 2004 U.S. PATENT DOCUMENTS Subclass Filing Date Date Class Document No. Name Examiner (If Initial appropriate) $\mathbf{A}\mathbf{A}$ AB FOREIGN PATENT DOCUMENTS Translation Country Date Examiner Document No. (Yes or No) Initial AC AD OTHER DOCUMENTS E.P. Gusev et al., "Ultrathin high-K gate stacks for advanced CMOS devices," International Electron Devices Meeting Technical Digest (2001), pp. 451-454. AE W. Zhu et al., "HfO2 and HfA1O for CMOS: Thermal Stability and Current AF Transport," International Electron Devices Meeting Technical Digest (2001), pp. 463-466. Y. Tamura et al., "Electrical characteristics of SiO₂/High-k stacked gate AG insulator," Extended Abstracts (The 49th Spring Meeting, 2002); The Japan Society of Applied Physics and Related Societies, No. 2, 28p-A-10, p.820.

Date Considered

8/18/05

Examiner